1.65V – 3.6V, 1x Ultra Low Power Mobile EMI Reduction IC

Features

- FCC approved method of EMI attenuation
- Proprietary "SaΦic™" technology, a non-PLL phase controlled Active EMI management architecture
- Generates a 1X low EMI Phase Modulated replication of the input signal.
- Vdd 1.65V - 3.6V 10 MHz to 40 MHz
- Multiple Deviation Selections
- Minimum frequency deviation selection capability
- Power Down Mode
- 8-pin WDFN package
- Supports automotive reliability standard: **AEC-Q100 Grade 1** and **Grade 2** certified

Product Description

The LX506 is a versatile 1x Active EMI management IC designed to provide system wide reduction of Electromagnetic Interference (EMI) and Radio Frequency Interference (RFI) from clock and data sources. The LX506 allows significant system cost savings by reducing the number of circuit board layers, ferrite beads, shielding and other passive components that are traditionally required to pass EMI regulations. The LX50x family of mobile active EMI management ICs is unique in it's design and is based on LFC's proprietary "SaΦic" phase controlled Active EMI management technology. This allows operation on aperiodic as well periodic signals. By the precise placement of the edges of the reconstructed input signal, the peak energy of the output is distributed over a wider and controlled energy band thereby significantly lowering system EMI compared to the typical narrow band signal produced by oscillators and most frequency generators.

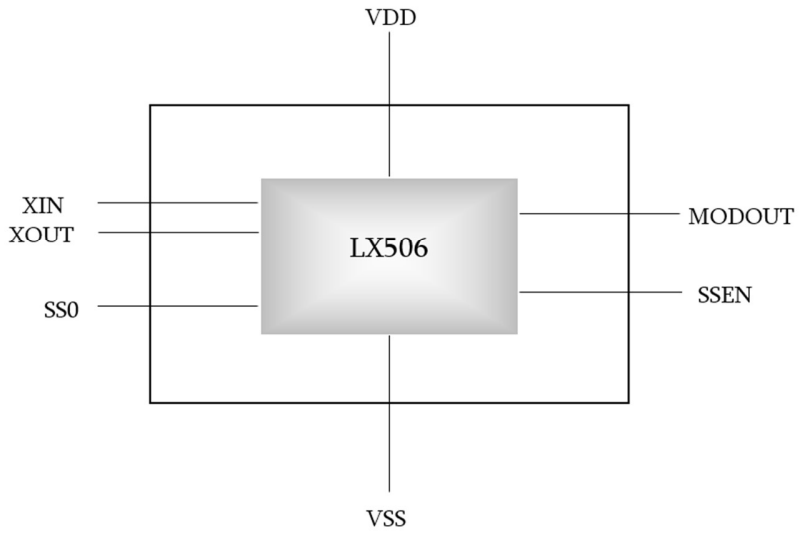
The LX506 has an input frequency range of 10 MHz to 40MHz over a wide voltage range of 1.65V to 3.6V. The device can be placed in a "non-modulated clock mode" by setting the SSEN pin to VDD where sets the MODOUT pin to no modulated clock output. The device has one "deviation control pins" SS0 to allow flexibility and optimization of both EMI compliance as well as in system design.

The device is available in an 8 pin DFN package.

Applications

The LX506 is targeted towards mobile platforms such as cell phones, MIDs, Netbooks and other "power and space" sensitive applications.

Block Diagram



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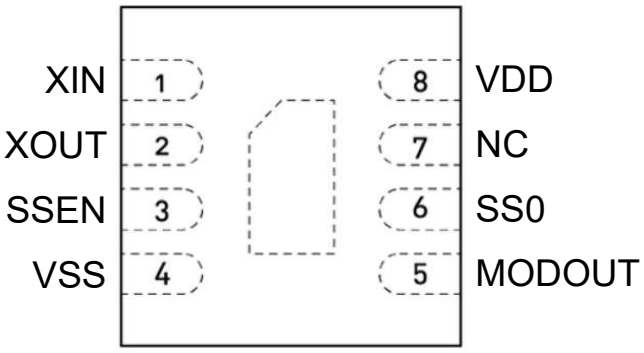
Pin Configuration



Pin Description

Pin#	Pin Name	Type	Description
1	XIN	I	Crystal Oscillator Input
2	XOUT	O	Crystal Oscillator Output
3	SSEN	I	Modulated Clock Output if Pull- Down. No Modulated Clock Output if Pull-Up. Internal Pull-Up Resistor
4	VSS	P	System ground reference input.
5	MODOUT	O	1X phase modulated buffered output.
6	SS0	I	Deviation Control Pin (refer Functionality Table) Internal Pull-Up Resistor. Recommend external Pull-Down Resistor 0Ω
7	NC	I	No Connection Pin
8	VDD	O	System Power Supply pin

Operating Conditions

Parameter	Description	Min	Max	Unit
V_{DD} (3.3V)	Supply Voltage	1.65	3.6	V
T_A	Operating Temperature (Ambient Temperature)	-40	+125	°C
C_L	Load Capacitance		20	pF
C_{IN}	Input Capacitance		5	pF

Note: Please refer to ordering information for T_A

Absolute Maximum Rating

Symbol	Parameter	Rating	Unit
Vin	Voltage on any pin with respect to Ground	-0.5 to +4.6	V
T_{STG}	Storage temperature	-65 to +125	°C
T_s	Max. Soldering Temperature (10 sec)	260	°C
T_J	Junction Temperature	150	°C
T_{DV}	Static Discharge Voltage (As per JEDEC STD22- A114-B)	2	KV

Note: These are stress ratings only and are not implied nor guaranteed for functional use. Exposure to absolute maximum ratings for prolonged periods of time may affect device reliability.

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Functional Table

Device	Vdd	Freq. Range (MHz)	Freq. (MHz)	Deviation (%)	
				SS0	SS0
				0	1
LX506	1.8	10~40	12	±0.18	±0.28
	1.8		24	±0.35	±0.55
	1.8		27	±0.40	±0.60
	1.8		30	±0.36	±0.55
	3.3	10~40	12	±0.10	±0.15
	3.3		24	±0.20	±0.30
	3.3		27	±0.22	±0.34
	3.3		30	±0.21	±0.33

Note: Specified at VDD 1.8V/3.3V and room temperature. Frequency deviation can vary over voltage and temperature by +/-20%

DC Electrical Characteristics (3.3V +/-0.3V)

Parameter	Description	Test Conditions		Min	Typ	Max	Unit
V_{DD}	Supply Voltage			3.0	3.3	3.6	V
V_{IH}	Input HIGH Voltage			0.66*V_{DD}			V
V_{IL}	Input LOW Voltage					0.33*V_{DD}	V
I_{IH}	Input HIGH Current (pins 3 and 6)	V_{IN} = V_{DD}				10	µA
I_{IL}	Input LOW Current (pins 3 and 6)	V_{IN} = 0V				10	µA
V_{OH}	Output HIGH Voltage	I_{OH} = -8mA		0.75*Vdd			V
V_{OL}	Output LOW Voltage	I_{OL} = +8mA				0.25*Vdd	V
I_{DD}	Dynamic Supply Current (SS1=0)	27 MHZ	Unloaded		11.0		mA
			15 pF load		13.0		
Z_o	Output Impedance				25		Ω
Deviation	Modulation	27MHz	1.8V	0.46		0.72	±
			3.3V	0.22		0.33	±

Switching Characteristics (3.3V +/-0.3V)

Parameter	Description	Test Conditions	Min	Typ	Max	Unit
INPUT	Input Frequency		10	24	40	MHz
MODOUT	Output Frequency		10	24	40	
T_d	Duty Cycle [1,2] = (t_2 / t_1) * 100	Measured at VDD /2	45	50	55	%
t_3	Output Rise Time [1,2]	Measured between 20% to 80%	0.8	1.8	2.8	nS
t_4	Output Fall Time [1,2]	Measured between 80% to 20%	1.0	2	3.0	nS

Notes:
1. All parameters specified with 27MHz without loaded outputs and V_{DD} 3.3V.
2. Parameter is guaranteed by design and characterization. Not 100% tested in production.

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DC Electrical Characteristics (1.8V +/-0.15V)

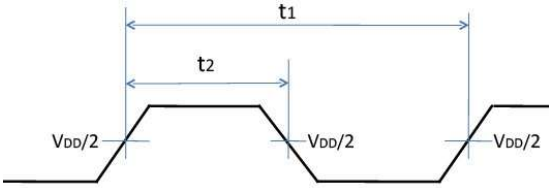
Parameter	Description	Test Conditions		Min	Typ	Max	Unit
V_{DD}	Supply Voltage			1.65	1.8	1.95	V
V_{IH}	Input HIGH Voltage			0.66*Vdd			V
V_{IL}	Input LOW Voltage					0.33*Vdd	V
I_{IH}	Input HIGH Current (pins 5 and 6)	V_{IN} = VDD				10	µA
I_{IL}	Input LOW Current (pins 5 and 6)	V_{IN} = 0V				10	µA
V_{OH}	Output HIGH Voltage	I_{OH} = -4mA		0.75*Vdd			V
V_{OL}	Output LOW Voltage	I_{OL} = +4mA				0.25*Vdd	V
I_{DD}	Dynamic Supply Current (SS0=1)	27 MHz	Unloaded		5.0		mA
			15 pF load		7.5		
Zo	Output Impedance				25		Ω

Switching Characteristics (1.8V +/-0.15V)

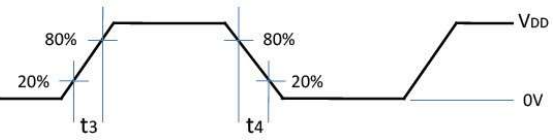
Parameter	Description	Test Conditions	Min	Typ	Max	Unit
INPUT	Input Frequency		10	24	40	MHz
MODOUT	Output Frequency		10	24	40	
T_d	Duty Cycle [1,2] = (t_2 / t_1) * 100	Measured at VDD /2	45	50	55	%
t_3	Output Rise Time [1,2]	Measured between 20% to 80%	1.2	2.2	TBD	nS
t_4	Output Fall Time [1,2]	Measured between 80% to 20%	1.2	2.2	TBD	nS

Notes:
1. All parameters specified with 27MHz without loaded outputs and V_{DD} 1.8V
2. Parameter is guaranteed by design and characterization. Not 100% tested in production

Duty Cycle Timing



All Outputs Rise/Fall Time



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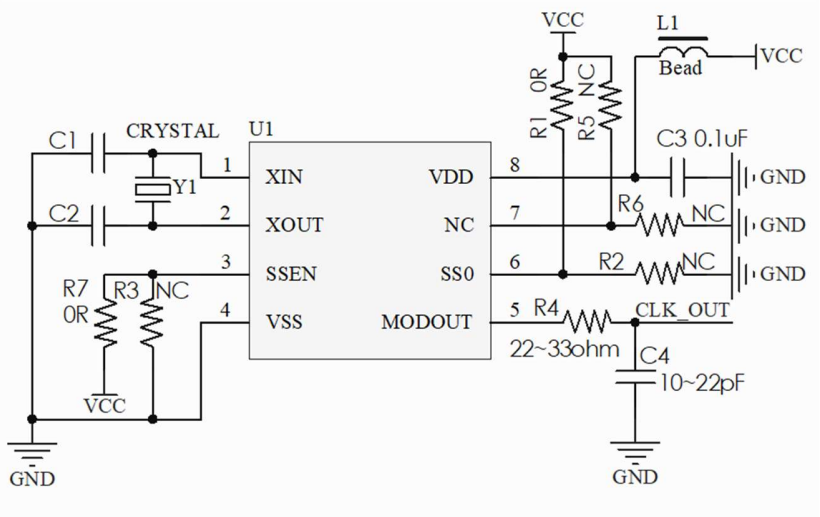
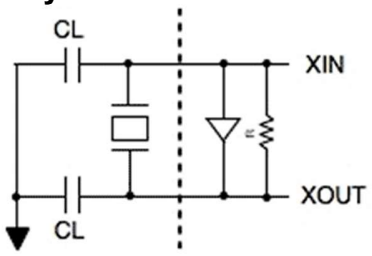
Application Schematic

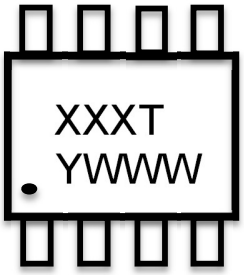


Crystal Oscillator Circuit



CL=2x(Cp-Cs)
Cp: load capacitance of Crystal
Cs: Stray capacitance (PCB trace + Input cap. of IC)

Marking Information



XXX: Part Number
T: Temperature Grade
Y: Year of Production
WWW: Work Order No.

Ordering Information

Part Number	Temp. Grade Indicator	Temp Grade	Temp Range	IC Marking	IC Package	Tape & Reel
LX506C	C	Commercial	0°~70°C	505C	2mm x 2mm 8L WDFN	4,000 pcs / Reel
LX506I	I	Industrial	-40°~85°C	505I		
LX506E	E	Automotive AEC Q100 Grade 2	-40°~105°C	505E		
LX506A	A	Automotive AEC Q100 Grade 1	-40°~125°C	505A		

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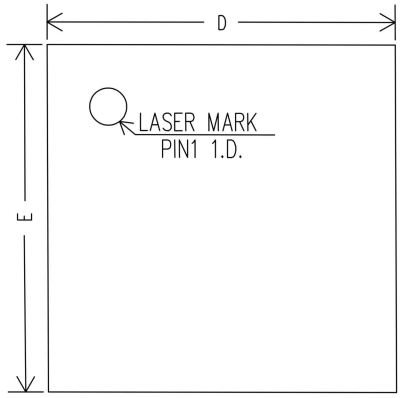
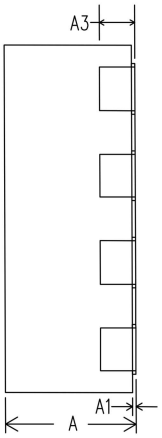
Package Dimension
WDFN



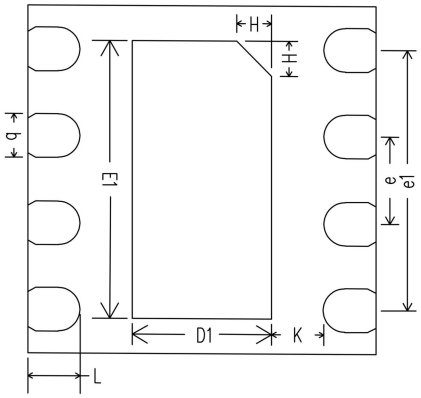
TOP VIEW



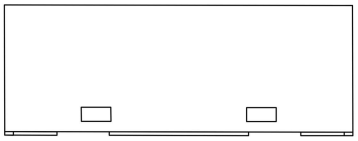
SIDE VIEW

COMMON DEMENSIONS
(UNITS OF MEASURE = MILLIMETER

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A3		0.203REF	
B	0.20	0.25	0.30
D	1.95	2.00	2.05
E	1.95	2.00	2.05
D1	0.75	0.80	0.85
E1	1.55	1.60	1.65
e	0.40	0.50	0.60
E1	1.40	1.50	1.60
H		0.20REF	
K	0.20	0.30	0.40
L	0.25	0.30	0.35



BOTTOM VIEW



SIDE VIEW

Revision History

Revision Number	Date of Release	Changes
1.0	10/25/2024	1) Preliminary specification

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